

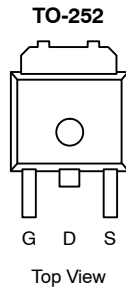
# IRLR3715TRRPBF-VB Datasheet

## N-Channel 20-V (D-S)175 °C MOSFET

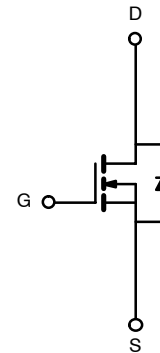
| PRODUCT SUMMARY |                           |                        |
|-----------------|---------------------------|------------------------|
| $V_{DS}$ (V)    | $r_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) <sup>a</sup> |
| 20              | 0.0045 @ $V_{GS} = 4.5$ V | 100                    |
|                 | 0.006 @ $V_{GS} = 2.5$ V  | 90                     |

### FEATURES

- Trench Power MOSFET
- 175°C Maximum Junction Temperature
- 100%  $R_g$  Tested



Drain Connected to Tab



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

| Parameter   | Symbol         | Limit   | Unit             |
|---|----------------|---|------------------|
| Drain-Source Voltage                                      | $V_{DS}$       | 20  | V                |
| Gate-Source Voltage                                       | $V_{GS}$       | $\pm 15$  |                  |
| Continuous Drain Current <sup>a</sup>                     | $I_D$          | $T_C = 25^\circ\text{C}$<br>100                 | A                |
|   |                | $T_C = 100^\circ\text{C}$<br>80                 |                  |
| Pulsed Drain Current                                      | $I_{DM}$       | 200   |                  |
| Continuous Source Current (Diode Conduction) <sup>a</sup> | $I_S$          | 65  |                  |
| Maximum Power Dissipation                                 | $P_D$          | $T_C = 25^\circ\text{C}$<br>71                  | W                |
|   |                | $T_A = 25^\circ\text{C}$<br>8.3 <sup>b, c</sup> |                  |
| Operating Junction and Storage Temperature Range          | $T_J, T_{stg}$ | -55 to 175                                      | $^\circ\text{C}$ |

### THERMAL RESISTANCE RATINGS

| Parameter                                | Symbol     | Typical                | Maximum | Unit               |
|--|------------|------------------------|---------|--------------------|
| Maximum Junction-to-Ambient <sup>b</sup> | $R_{thJA}$ | $t \leq 10$ sec.<br>15 | 18      | $^\circ\text{C/W}$ |
|  |            | Steady State<br>40     | 50      |                    |
| Maximum Junction-to-Case                 | $R_{thJC}$ | 1.75                   | 2.1     |                    |

#### Notes

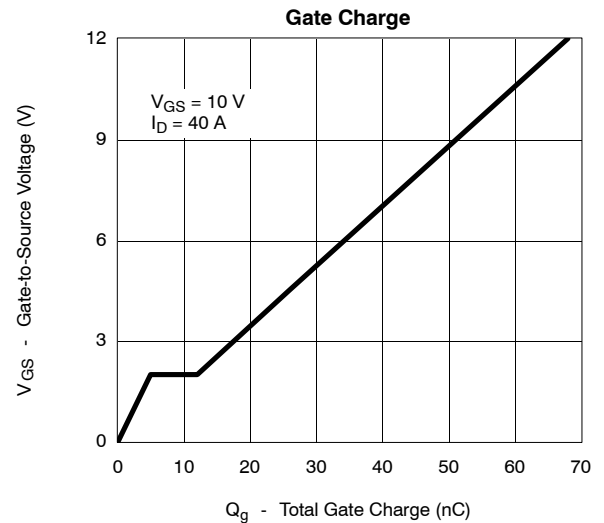
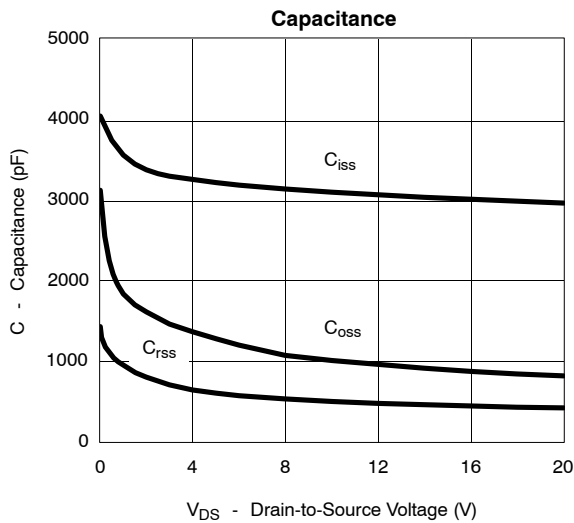
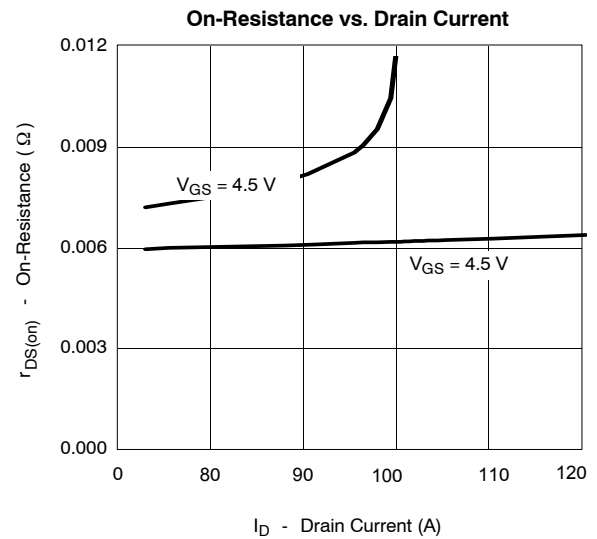
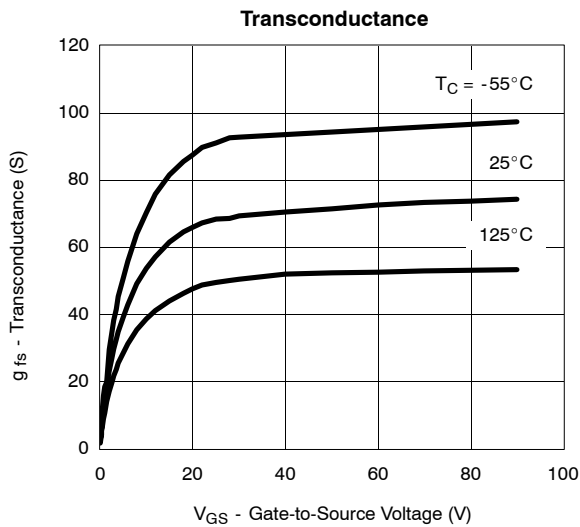
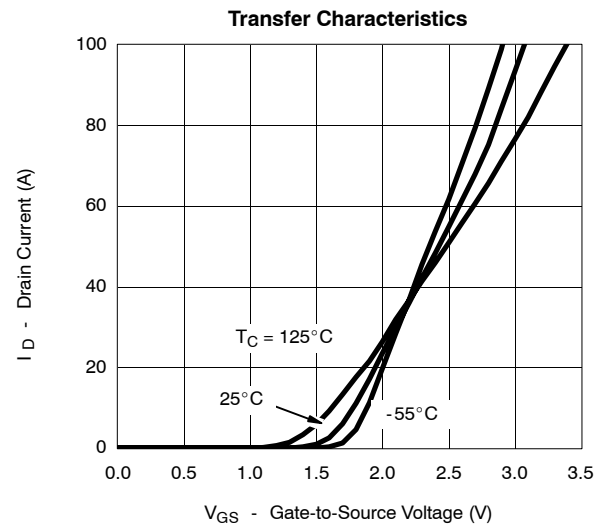
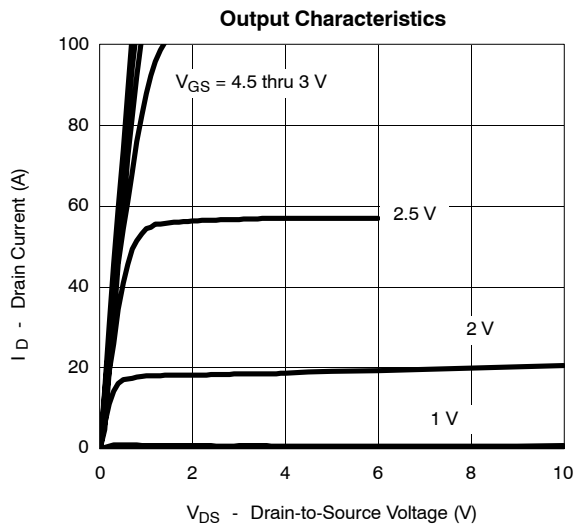
- a. Package Limited  
 b. Surface Mounted on 1" x 1" FR4 Board  
 c.  $t \leq 10$  sec

| SPECIFICATIONS (T <sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)         |                      |  |     |                  |       |      |
|--|----------------------|--|-----|------------------|-------|------|
| Parameter  | Symbol               | Test Condition   | Min | Typ <sup>a</sup> | Max   | Unit |
| Static   |                      |  |     |                  |       |      |
| Drain-Source Breakdown Voltage   | V <sub>(BR)DSS</sub> | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA   | 20  |                  |       | V    |
| Gate Threshold Voltage   | V <sub>GS(th)</sub>  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA  | 0.5 |                  | 1.5   |      |
| Gate-Body Leakage  | I <sub>GSS</sub>     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V  |     |                  | ± 100 | nA   |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>     | V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V  |     |                  | 1     | μA   |
|  |                      | V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C   |     |                  | 50    |      |
| On-State Drain Current <sup>b</sup>                                    | I <sub>D(on)</sub>   | V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 4.5 V   | 100 |                  |       | A    |
| Drain-Source On-State Resistance <sup>b</sup>                          | r <sub>DS(on)</sub>  | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A   |     | 0.0045           |       | Ω    |
|  |                      | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C  |     | 0.0055           |       |      |
|  |                      | V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 20 A   |     | 0.006            |       |      |
| Forward Transconductance <sup>b</sup>                                  | g <sub>fs</sub>      | V <sub>DS</sub> = 5 V, I <sub>D</sub> = 40 A   | 20  |                  |       | S    |
| Dynamic <sup>a</sup>   |                      |  |     |                  |       |      |
| Input Capacitance  | C <sub>iss</sub>     | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 20 V, f = 1 MHz   |     | 3660             |       | pF   |
| Output Capacitance   | C <sub>oss</sub>     |  |     | 730              |       |      |
| Reverse Transfer Capacitance   | C <sub>rss</sub>     |  |     | 375              |       |      |
| Total Gate Charge <sup>c</sup>   | Q <sub>g</sub>       | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 40 A   |     | 26               | 35    | nC   |
| Gate-Source Charge <sup>c</sup>  | Q <sub>gs</sub>      |  |     | 5                |       |      |
| Gate-Drain Charge <sup>c</sup>   | Q <sub>gd</sub>      |  |     | 7                |       |      |
| Gate Resistance  | R <sub>g</sub>       |  | 1   |                  | 3.7   | Ω    |
| Turn-On Delay Time <sup>c</sup>  | t <sub>d(on)</sub>   | V <sub>DD</sub> = 10 V, R <sub>L</sub> = 0.25 Ω<br>I <sub>D</sub> ≅ 40 A, V <sub>GEN</sub> = 4.5 V, R <sub>G</sub> = 2.5 Ω |     | 20               | 35    | ns   |
| Rise Time <sup>c</sup>   | t <sub>r</sub>       |  |     | 120              | 190   |      |
| Turn-Off Delay Time <sup>c</sup>                                       | t <sub>d(off)</sub>  |  |     | 45               | 70    |      |
| Fall Time <sup>c</sup>   | t <sub>f</sub>       |  |     | 20               | 35    |      |
| Source-Drain Diode Ratings and Characteristic (T <sub>C</sub> = 25 °C) |                      |  |     |                  |       |      |
| Pulsed Current   | I <sub>SM</sub>      |  |     |                  | 100   | A    |
| Diode Forward Voltage <sup>b</sup>                                     | V <sub>SD</sub>      | I <sub>F</sub> = 100 A, V <sub>GS</sub> = 0 V  |     | 1.2              | 1.5   | V    |
| Source-Drain Reverse Recovery Time                                     | t <sub>rr</sub>      | I <sub>F</sub> = 40 A, di/dt = 100 A/μs  |     | 35               | 70    | ns   |

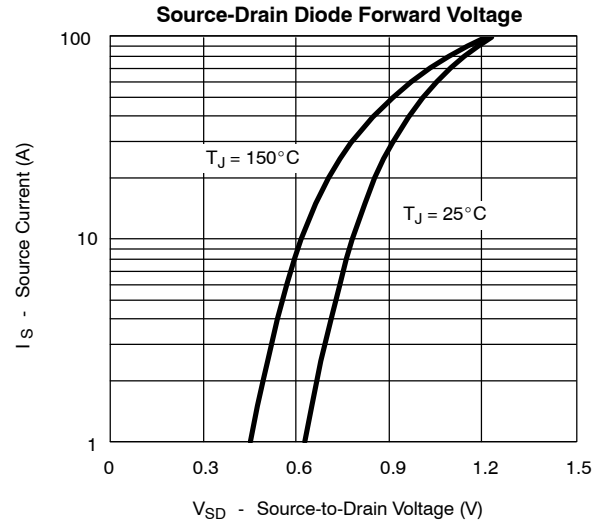
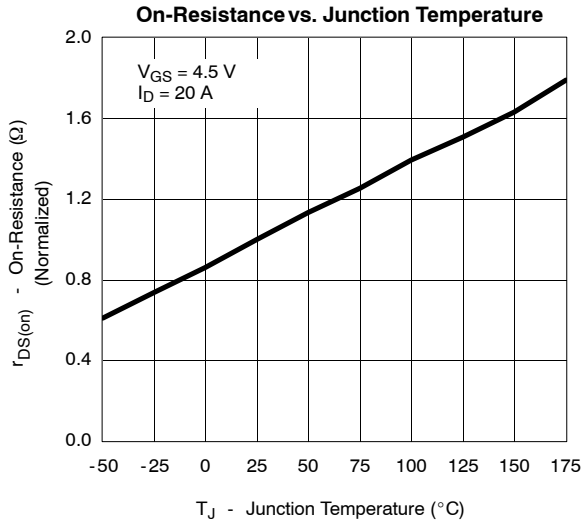
## Notes

- a. Guaranteed by design, not subject to production testing.  
 b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
 c. Independent of operating temperature.

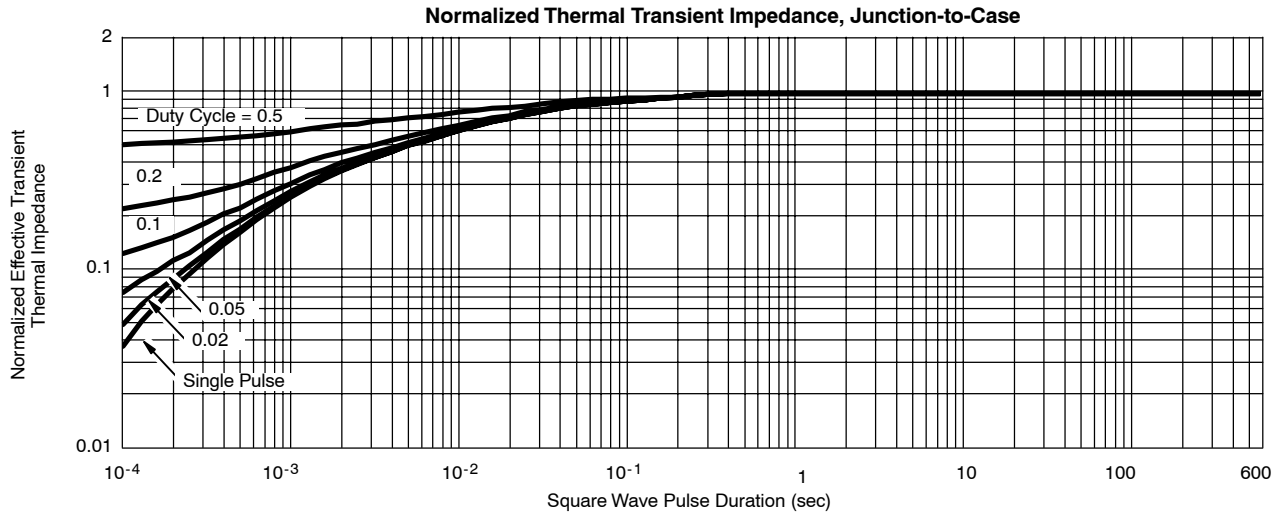
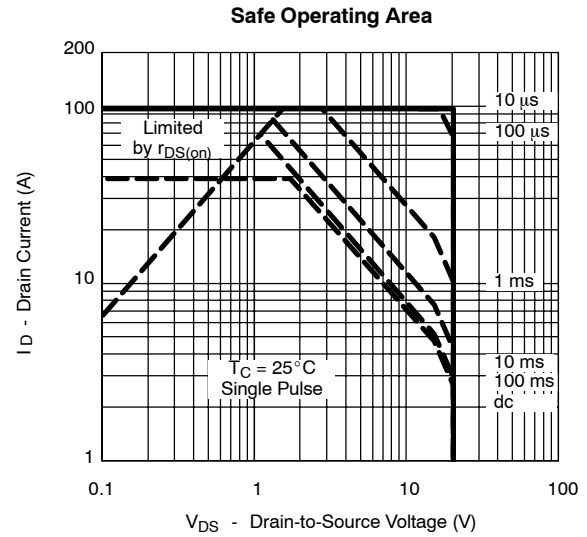
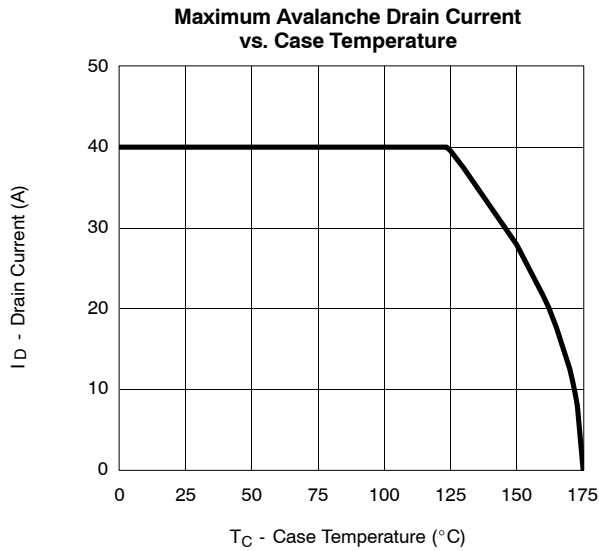
**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**



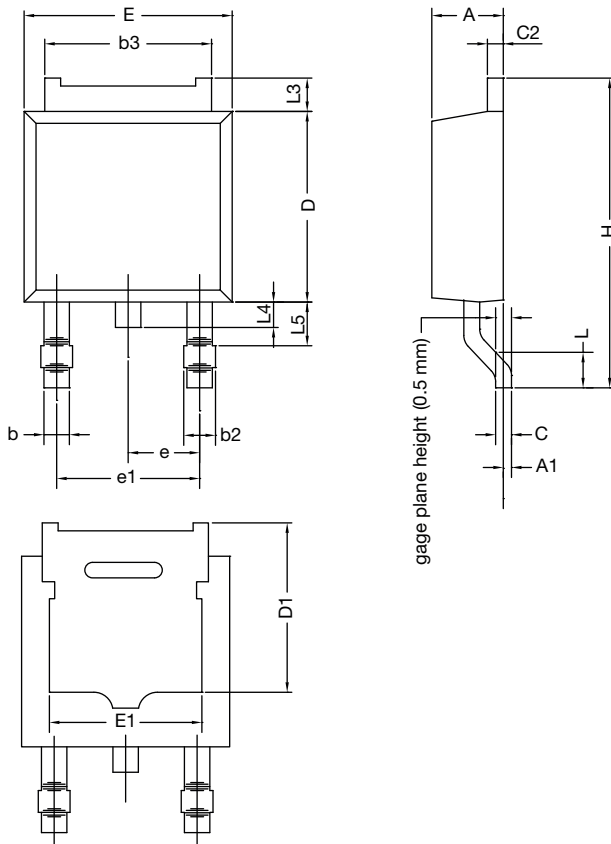
**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



**THERMAL RATINGS**



## TO-252AA CASE OUTLINE



| DIM.   | MILLIMETERS |       | INCHES    |       |
|--|-------------|-------|-----------|-------|
|  | MIN.        | MAX.  | MIN.      | MAX.  |
| A  | 2.18        | 2.38  | 0.086     | 0.094 |
| A1   | -           | 0.127 | -         | 0.005 |
| b  | 0.64        | 0.88  | 0.025     | 0.035 |
| b2   | 0.76        | 1.14  | 0.030     | 0.045 |
| b3   | 4.95        | 5.46  | 0.195     | 0.215 |
| C  | 0.46        | 0.61  | 0.018     | 0.024 |
| C2   | 0.46        | 0.89  | 0.018     | 0.035 |
| D  | 5.97        | 6.22  | 0.235     | 0.245 |
| D1   | 5.21        | -     | 0.205     | -     |
| E  | 6.35        | 6.73  | 0.250     | 0.265 |
| E1   | 4.32        | -     | 0.170     | -     |
| H  | 9.40        | 10.41 | 0.370     | 0.410 |
| e  | 2.28 BSC    |       | 0.090 BSC |       |
| e1   | 4.56 BSC    |       | 0.180 BSC |       |
| L  | 1.40        | 1.78  | 0.055     | 0.070 |
| L3   | 0.89        | 1.27  | 0.035     | 0.050 |
| L4   | -           | 1.02  | -         | 0.040 |
| L5   | 1.14        | 1.52  | 0.045     | 0.060 |
| ECN: X12-0247-Rev. M, 24-Dec-12<br>DWG: 5347 |             |       |           |       |

### Note

- Dimension L3 is for reference only.

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